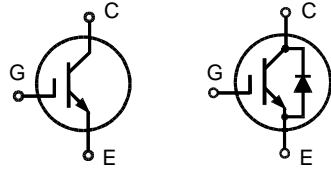


# High Voltage IGBT with optional Diode

**IXDP 20N60 B**  
**IXDP 20N60 BD1**

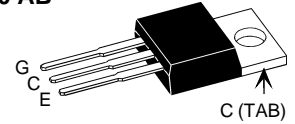
**$V_{CES} = 600\text{ V}$**   
 **$I_{C25} = 32\text{ A}$**   
 **$V_{CE(sat) typ} = 2.2\text{ V}$**

High Speed,  
Low Saturation Voltage



IXDP 20N60B IXDP 20N60B D1

**TO-220 AB**



G = Gate,  
C = Collector ,  
E = Emitter  
TAB = Collector

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 20\text{ k}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	32	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	20	A
$I_{CM}$	$T_C = 90^\circ\text{C}, t_p = 1\text{ ms}$	40	A
<b>RBSOA</b>	$V_{GE} = \pm 15\text{ V}, T_J = 125^\circ\text{C}, R_G = 22\ \Omega$ Clamped inductive load, $L = 30\ \mu\text{H}$	$I_{CM} = 60$ $V_{CEK} < V_{CES}$	A
<b><math>t_{SC}</math> (SCSOA)</b>	$V_{GE} = \pm 15\text{ V}, V_{CE} = 600\text{ V}, T_J = 125^\circ\text{C}$ $R_G = 22\ \Omega$ , non repetitive	10	$\mu\text{s}$
<b><math>P_C</math></b>	$T_C = 25^\circ\text{C}$	IGBT Diode	140 50 W W
<b><math>T_J</math></b>		-55 ... +150	$^\circ\text{C}$
<b><math>T_{stg}</math></b>		-55 ... +150	$^\circ\text{C}$
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
<b><math>M_d</math></b>	Mounting torque	0.4 - 0.6	Nm
<b>Weight</b>		2	g

## Features

- NPT IGBT technology
- low switching losses
- low tail current
- no latch up
- short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- International standard package

## Advantages

- Space savings
- High power density

## Typical Applications

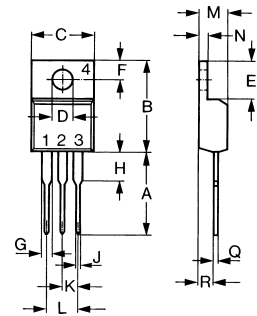
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 0.4\text{ mA}, V_{CE} = V_{GE}$	3		5 V
$I_{CES}$	$V_{CE} = V_{CES}$		$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	0.1 mA mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 500\text{ nA}$
$V_{CE(sat)}$	$I_C = 20\text{ A}, V_{GE} = 15\text{ V}$	2.2	2.8	V

Symbol	Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
C <sub>ies</sub>	V <sub>CE</sub> = 25 V, V <sub>GE</sub> = 0 V, f = 1 MHz		800	pF
C <sub>oes</sub>			85	pF
C <sub>res</sub>			50	pF
Q <sub>g</sub>	I <sub>C</sub> = 20 A, V <sub>GE</sub> = 15 V, V <sub>CE</sub> = 480 V		70	nC
t <sub>d(on)</sub>	Inductive load, T <sub>J</sub> = 125°C I <sub>C</sub> = 20 A, V <sub>GE</sub> = ±15 V, V <sub>CE</sub> = 300 V, R <sub>G</sub> = 22 Ω		25	ns
t <sub>r</sub>			30	ns
t <sub>d(off)</sub>			260	ns
t <sub>f</sub>			55	ns
E <sub>on</sub>			0.9	mJ
E <sub>off</sub>		0.4	mJ	
R <sub>thJC</sub>	Package with heatsink compound			0.9 K/W
R <sub>thCH</sub>		0.5		K/W

**Reverse Diode (FRED) [D1 version only]**

Symbol	Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>F</sub>	I <sub>F</sub> = 20 A, V <sub>GE</sub> = 0 V		2.1	2.4 V
	I <sub>F</sub> = 20 A, V <sub>GE</sub> = 0 V, T <sub>J</sub> = 125°C		1.6	V
I <sub>F</sub>	T <sub>C</sub> = 25°C			25 A
	T <sub>C</sub> = 90°C			15 A
I <sub>RM</sub>	I <sub>F</sub> = 10 A, -di <sub>F</sub> /dt = 400 A/μs, V <sub>R</sub> = 300 V		11	A
t <sub>rr</sub>	V <sub>GE</sub> = 0 V, T <sub>J</sub> = 125°C		80	ns
t <sub>rr</sub>	I <sub>F</sub> = 1 A, -di <sub>F</sub> /dt = 100 A/μs, V <sub>R</sub> = 30 V, V <sub>GE</sub> = 0 V		40	ns
R <sub>thJC</sub>				2.5 K/W

**TO-220 AB Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

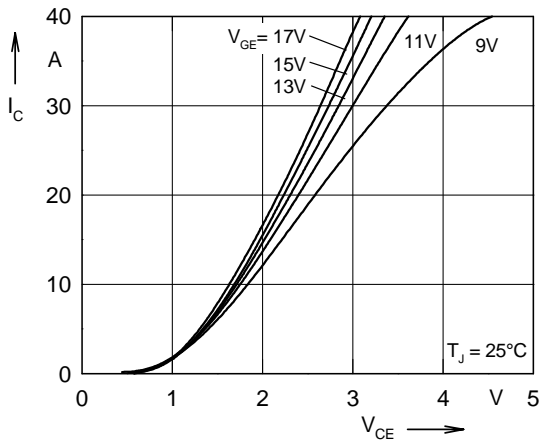


Fig. 1 Typ. output characteristics

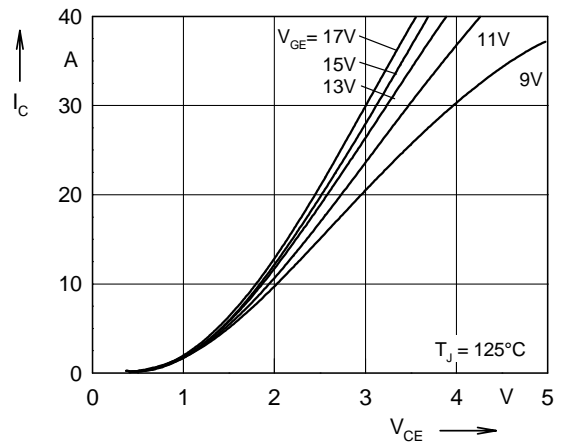


Fig. 2 Typ. output characteristics

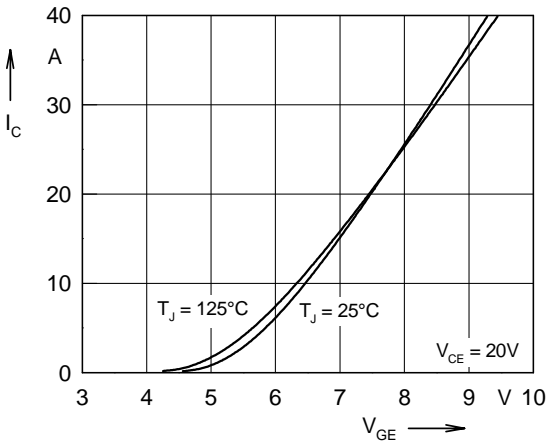


Fig. 3 Typ. transfer characteristics

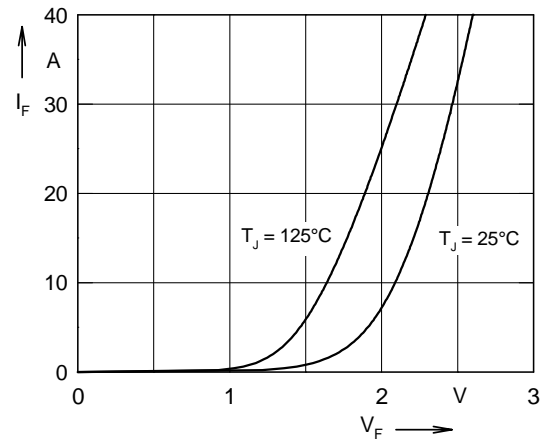


Fig. 4 Typ. forward characteristics of free wheeling diode

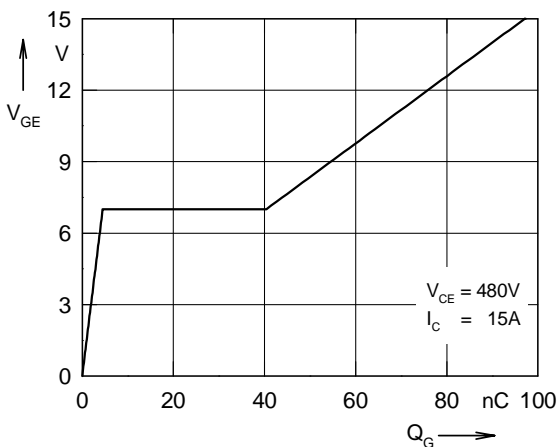


Fig. 5 Typ. turn on gate charge

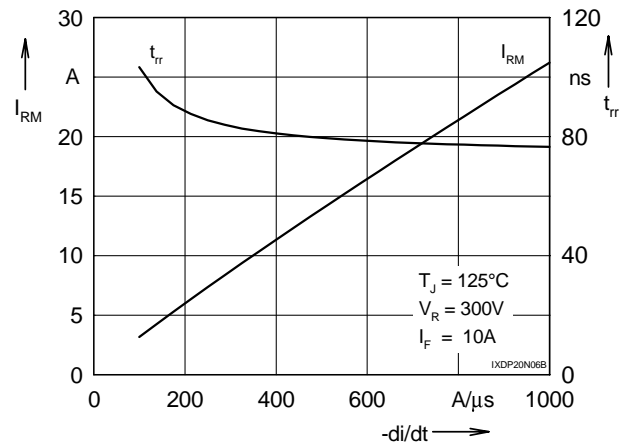


Fig. 6 Typ. turn off characteristics of free wheeling diode

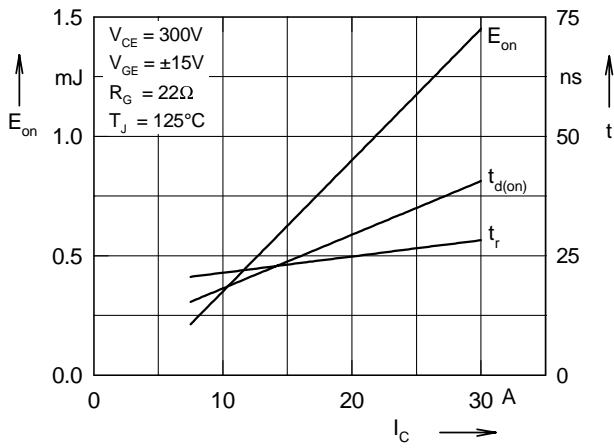


Fig. 7 Typ. turn on energy and switching times versus collector current

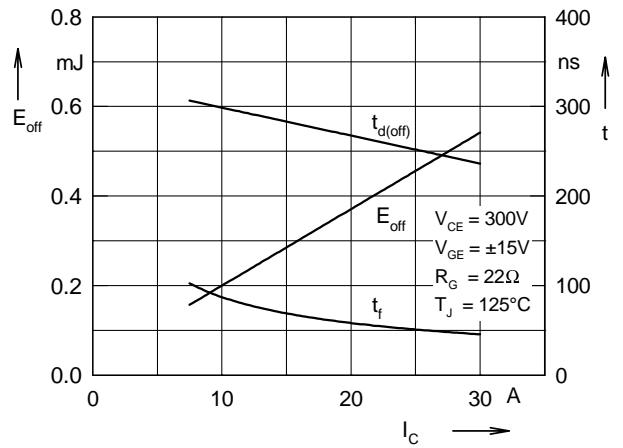


Fig. 8 Typ. turn off energy and switching times versus collector current

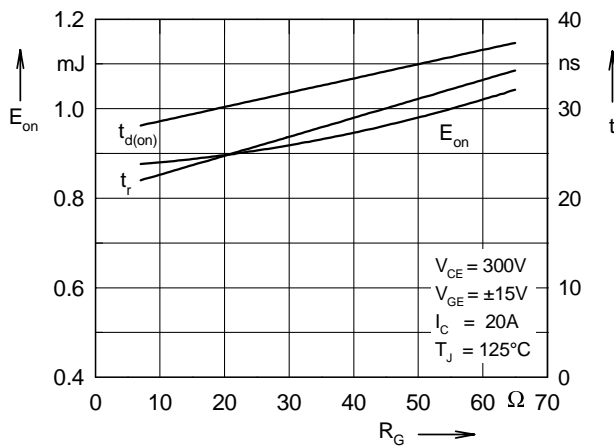


Fig. 9 Typ. turn on energy and switching times versus gate resistor

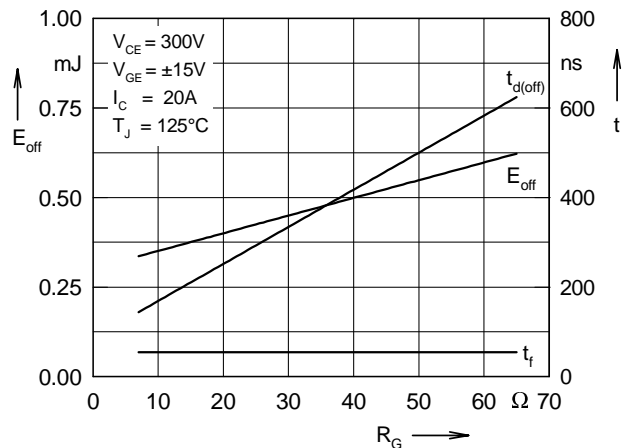


Fig.10 Typ. turn off energy and switching times versus gate resistor

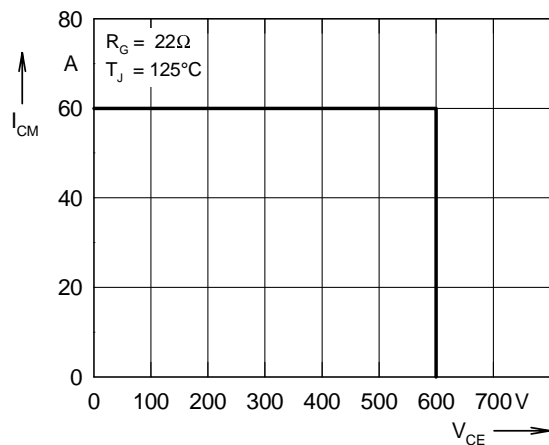


Fig. 11 Reverse biased safe operating area RBSOA

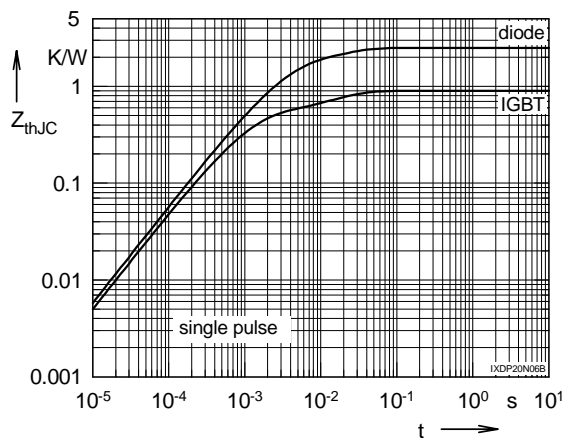


Fig. 12 Typ. transient thermal impedance